

μPD166020T1F

MOS INTEGRATED CIRCUIT

 R07DS0441EJ0100
 Rev.1.00
 Aug 15, 2011

1. Overview

1.1 Description

The μPD166020T1F is a single N-channel high-side switch with charge pump, diagnostic feedback with load current sense and embedded protection functions.

1.2 Features

- Built-in charge pump
- Low on-state resistance
- Short circuit protection
 - Shutdown by over current detection and over load detection
- Over temperature protection
 - Shutdown with auto-restart on cooling
- Built-in diagnostic function
 - Proportional load current sensing
 - Defined fault signal in case of abnormal load condition
- Under voltage lock out
- Reverse battery protection by self turn on of N-ch MOSFET
- Small multi-chip package: JEDEC 5-pin TO-252 (MSL: 3, profile acc. J-STD-20C)
- AEC Qualified

1.3 Applications

- Light bulb (to 65 W) switching
- Switching of all types of 14 V DC grounded loads, such as LED, inductor, resistor and capacitor
- Replacement for fuse and relay

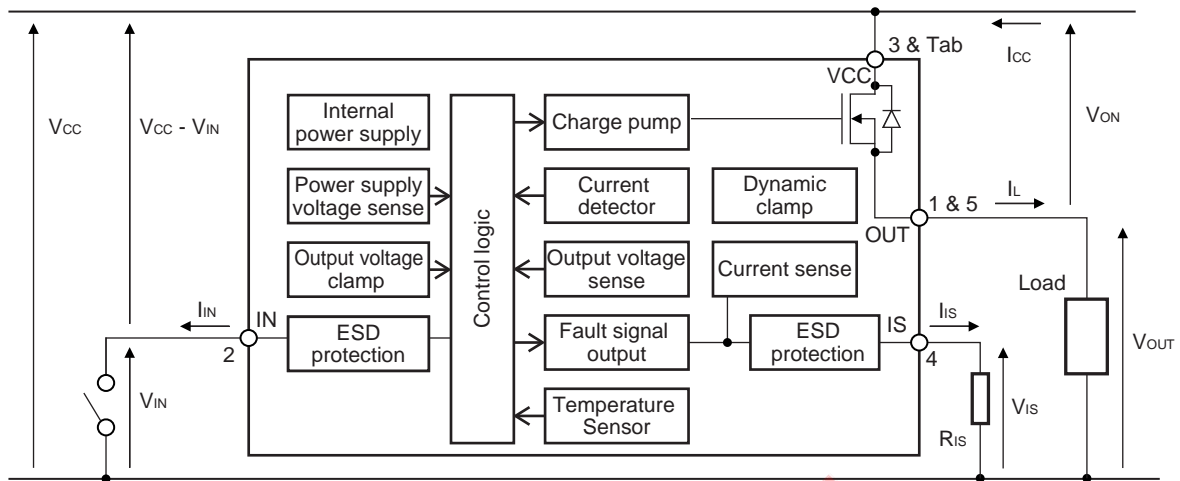
2. Ordering Information

Part No.	Lead plating	Packing	Package
μ PD166020T1F-E1-AY *1	Sn	Tape 2500 p/reel	5-pin TO-252 (MP-3ZK)

Note: *1. Pb-free (This product does not contain Pb in the external electrode.)

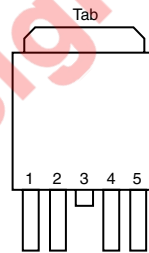
3. Specification

3.1 Block Diagram



3.2 Pin Configuration

Pin No.	Terminal Name
1	OUT
2	IN
3/Tab	VCC
4	IS
5	OUT



Pin Function

Terminal Name	Pin function	Recommended connections
OUT	Output to load	Pin 1 and Pin 5 must be externally shorted
IN	Activates the output, if it shorted to ground	If reverse battery protection feature is used, refer to 3.6.3 Power Dissipation Under Reverse Battery Condition .
VCC	Supply Voltage; tab and pin 3 are internally shorted	Connected to battery voltage with small 100 nF capacitor in parallel
IS	Sense output, diagnostic feedback	If current sense and diagnostic feature are not used, connected to GND via resistor

3.3 Absolute Maximum Ratings

T_A = 25°C, unless otherwise specified

Parameter	Symbol	Rating	Unit	Test Conditions	
V _{CC} Voltage	V _{CC1}	28	V		
V _{CC} voltage under Load Dump condition	V _{CC2}	42	V	R _I = 1 Ω, R _L = 1.5 Ω, R _{IS} = 1 kΩ, t _d = 400 ms	
V _{CC} Voltage at reverse battery condition	-V _{CC}	-16	V	R _L = 2.2 Ω, 1 min.	
Load Current (Short circuit current)	I _{L(SC)}	Self limited	A		
Power dissipation (DC)	P _D	1.2	W	T _A = 85°C, Device on 50 mm x 50 mm x 1.5 mm epoxy PCB FR4 with 6 cm ² of 70 μm copper area	
Voltage of IN pin	V _{IN}	V _{CC} - 28	V	DC	
		V _{CC} + 14		At reverse battery condition, t < 1 min.	
Voltage of IS pin	V _{IS}	V _{CC} - 28	V	DC	
		V _{CC} + 14		At reverse battery condition, t < 1 min.	
Inductive load switch-off energy dissipation single pulse	E _{AS1}	50	mJ	V _{CC} = 12 V, I _L = 10 A, T _{ch,start} ≤ 150°C refer to 3.6.8 Inductive Load Switch Off Energy Dissipation for a Single Pulse	
Maximum allowable energy dissipation at shutdown operation	E _{AS2}	105	mJ	V _{CC} = 18 V, T _{ch,start} ≤ 150°C, L _{supply} = 5 μH, L _{short} = 15 μH refer to 3.6.9 Maximum Allowable Switch off Energy (Single Pulse)	
Channel Temperature	T _{ch}	-40 to +150	°C		
Dynamic temperature increase while switching	ΔT _{ch}	60	°C		
Storage Temperature	T _{stg}	-55 to +150	°C		
ESD susceptibility	V _{ESD}	2000	V	HBM	AEC-Q100-002 std. R = 1.5 kΩ, C = 100 pF
		400	V	MM	AEC-Q100-003 std. R = 0 Ω, C = 200 pF

3.4 Thermal Characteristics

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Thermal characteristics	R _{th(ch-a)}		45		°C/W	Device on 50 mm x 50mm x 1.5 mm epoxy PCB FR4 with 6 cm ² of 70 μm copper area
	R _{th(ch-c)}			3.17	°C/W	

3.5 Electrical Characteristics

Operation Function

$T_{ch} = 25^{\circ}\text{C}$, $V_{CC} = 12\text{ V}$, unless otherwise specified

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Required current capability of Input switch	I_{IH}		1.0	2.2	mA	$T_{ch} = -40$ to 150°C
Input current for turn-off	I_{IL}			50	μA	
Standby Current	$I_{CC(\text{off})}$		2.5	5.0	μA	$R_L = 2.2\ \Omega$, $I_{in} = 0\ \text{A}$, $T_{ch} = 25^{\circ}\text{C}$
			2.5	15.0	μA	$R_L = 2.2\ \Omega$, $I_{in} = 0\ \text{A}$, $T_{ch} = -40$ to 150°C
On State Resistance	R_{on}		8	10	m Ω	$I_L = 7.5\ \text{A}$, $T_{ch} = 25^{\circ}\text{C}$
			14	18		$I_L = 7.5\ \text{A}$, $T_{ch} = 150^{\circ}\text{C}$
Output voltage drop limitation at small load current	$V_{on(\text{NL})}$		30	65	mV	$T_{ch} = -40$ to 150°C
Turn On Time	t_{on}		120	360	μs	$R_L = 2.2\ \Omega$, $T_{ch} = -40$ to 150°C , refer to 3.6.6 Measurement Condition
Turn Off Time	t_{off}		250	500	μs	
Slew rate on *1	$dv/dton$		0.2	0.8	V/ μs	25 to 50 % V_{OUT} , $R_L = 2.2\ \Omega$, $T_{ch} = -40$ to 150°C , refer to 3.6.6 Measurement Condition
Slew rate off *1	$-dv/dtoff$		0.2	0.6	V/ μs	50 to 25 % V_{OUT} , $R_L = 2.2\ \Omega$, $T_{ch} = -40$ to 150°C , refer to 3.6.6 Measurement Condition

Note: *1. Not tested, specified by design

Not recommended for new designs

Protection Function

T_{ch} = 25°C, V_{CC} = 12 V, unless otherwise specified

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
On-state resistance at reverse battery condition *1	R _{on(rev)}		9.5	13	mΩ	T _{ch} = 25°C
			16	22	mΩ	T _{ch} = 150°C
Short circuit detection current	I _{L6,3(SC)} *1		50	120	A	T _{ch} = -40°C
			50			T _{ch} = 25°C
		20	45			T _{ch} = 150°C
	I _{L6,6(SC)} *1		35	110		T _{ch} = -40°C
			35			T _{ch} = 25°C
		10	35			T _{ch} = 150°C
	I _{L12,3(SC)}		110	180		T _{ch} = -40°C
			76	105		T _{ch} = 25°C
			50	95		T _{ch} = 150°C
	I _{L12,6(SC)} *1		90	160		T _{ch} = -40°C
			85			T _{ch} = 25°C
		40	80			T _{ch} = 150°C
	I _{L12,12(SC)} *1		55	120		T _{ch} = -40°C
			50			T _{ch} = 25°C
		10	45			T _{ch} = 150°C
	I _{L18,3(SC)} *1		130	200		T _{ch} = -40°C
			125			T _{ch} = 25°C
		60	110			T _{ch} = 150°C
	I _{L18,6(SC)} *1		110	170		T _{ch} = -40°C
			110			T _{ch} = 25°C
		50	110			T _{ch} = 150°C
	I _{L18,12(SC)} *1		75	120		T _{ch} = -40°C
			70			T _{ch} = 25°C
		30	65			T _{ch} = 150°C
I _{L18,18(SC)} *1		50	90	T _{ch} = -40°C		
		50		T _{ch} = 25°C		
	5	45		T _{ch} = 150°C		
Turn-on check delay after input current positive slope *1	t _{d(OC)}	0.9	2.1	3.8	ms	T _{ch} = -40 to 150°C
Remaining Turn-on check delay after turn-on time *1	t _{d(OC)} - t _{on}	0.65	1.6		ms	R _L = 2.2 Ω, T _{ch} = -40 to 150°C
Over load detection voltage	V _{on(OvL)}	0.65	1	1.45	V	T _{ch} = -40 to 150°C
Under voltage shutdown	V _{CIN(UV)}			5.5	V	T _{ch} = -40°C
		3.2	4.0	5.35	V	T _{ch} = 25°C
		2.7			V	T _{ch} = 150°C
Under voltage restart of charge pump	V _{CIN(CPr)}			6.3	V	T _{ch} = -40°C
		3.6	4.5	6.2	V	T _{ch} = 25°C
		3.2			V	T _{ch} = 150°C
Output clamp voltage (inductive load switch off)	V _{on(CL)}	30	34	40	V	I _L = 40 mA, T _{ch} = -40 to 150°C
Thermal shutdown temperature *1	T _{th}	150	175		°C	
Thermal hysteresis *1	ΔT _{th}		10		°C	

Note: *1. Not tested, specified by design

Diagnosis Function

T_{ch} = 25°C, V_{CC} = 12 V, unless otherwise specified

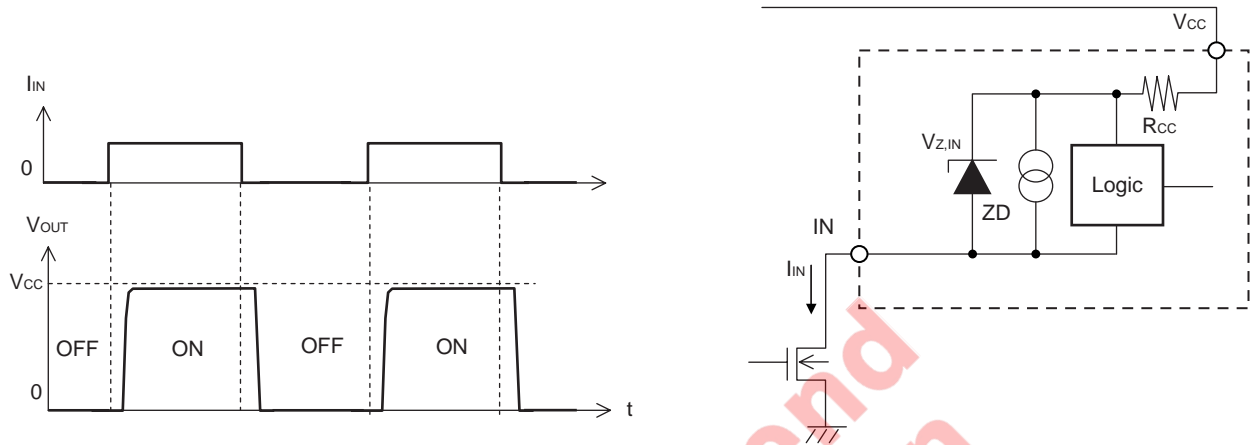
Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions			
Current sense ratio	K _{ILIS}					K _{ILIS} = I _L /I _{IS} , I _{IS} < I _{IS,lim}			
		8300	9200	11000		T _{ch} = -40°C	I _L = 30A		
		8300	9200	10600		T _{ch} = 25°C			
		8400	9300	10200		T _{ch} = 150°C			
				7500	9200	11400		T _{ch} = -40°C	I _L = 7.5 A
				8000	9300	10800		T _{ch} = 25°C	
				8300	9300	10400		T _{ch} = 150°C	
				7100	10200	13400		T _{ch} = -40°C	I _L = 2.5 A
				7700	10000	12500		T _{ch} = 25°C	
				8000	9800	12000		T _{ch} = 150°C	
				5000	12000	21000		T _{ch} = -40°C	
				5500	11500	17000		T _{ch} = 25°C	I _L = 0.5 A
6000	11500			16000		T _{ch} = 150°C			
Sense current offset current	I _{IS,offset}		0.1	1	μA	V _{IN} = 0 V, I _L = 0 A			
Sense current under fault condition	I _{IS,fault}	3.5	6.0	12.0	mA	Under fault conditions 8 V < V _{CC} - V _{IS} < 12 V, T _{ch} = -40 to 150°C			
Sense current saturation current	I _{IS,lim}	3.5	7.0	12.0	mA	V _{IS} < V _{OUT} - 6 V, T _{ch} = -40 to 150°C			
Fault Sense Signal delay after short circuit detection *1	t _{sdelay(fault)}		2	6	μs	T _{ch} = -40 to 150°C			
Sense current leakage current	I _{IS(LL)}		0.1	0.5	μA	I _{IN} = 0 A			
Current sense settling time to I _{IS} (static) after input current positive slope *1	t _{son(IS)}			700	μs	T _{ch} = -40 to 150°C, I _{IN} = 0 A ⊓ I _{IH} , R _L = 2.2 Ω			
Current sense settling time during on condition *1	T _{sic(IS)}		50	100	μs	T _{ch} = -40 to 150°C, I _L = 10A ⊓ 20 A			

Note: *1. Not tested, specified by design

3.6 Feature Description

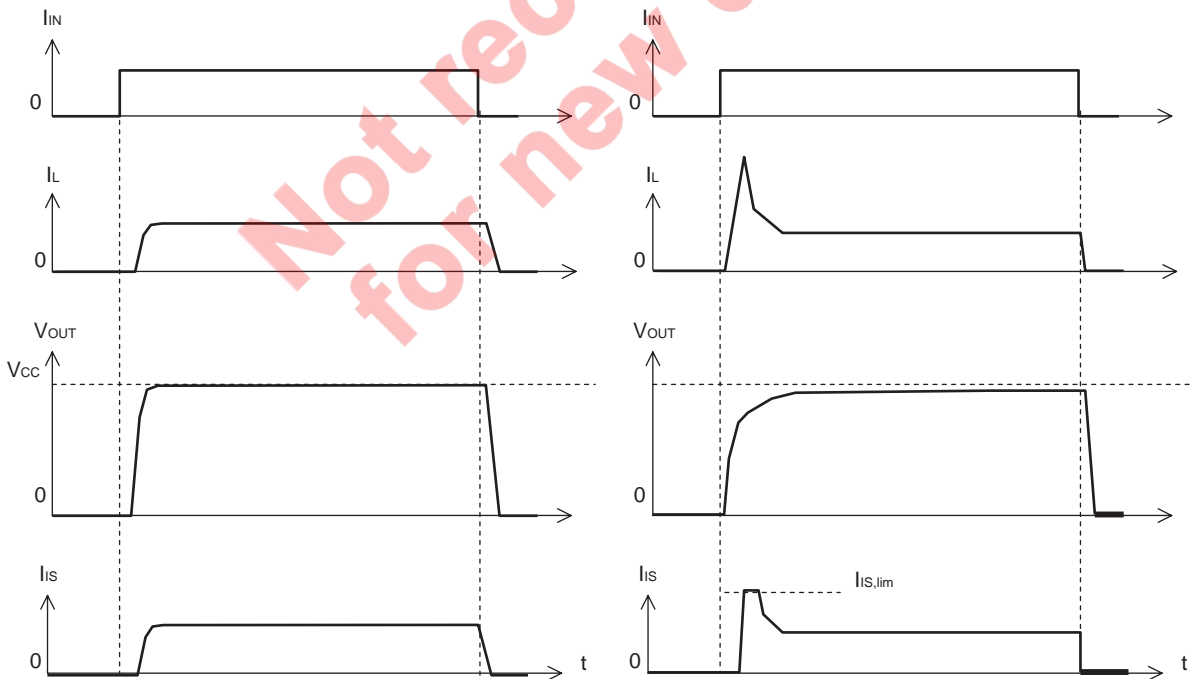
3.6.1 Driving Circuit

The high-side output is turned on, if the input pin is shorted to ground. The input current is below I_{IH} . The high-side output is turned off, if the input pin is open or the input current is below I_{IL} . R_{CC} is 100 Ω TYP. ESD protection diode: 46 V TYP.

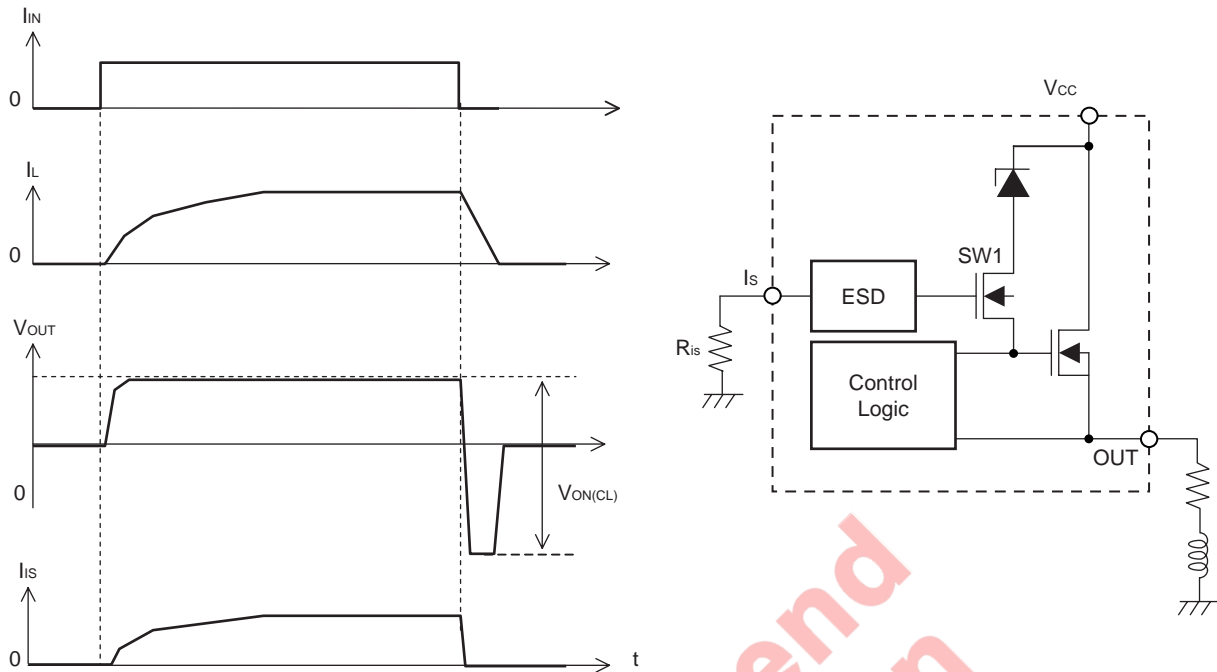


Switching a resistive load

Switching lamps



Switching an inductive load



Dynamic clamp operation at inductive load switch off

The dynamic clamp circuit works only when the inductive load is switched off. When the inductive load is switched off, the voltage of OUT falls below 0 V. The gate voltage of SW1 is then nearly equal to GND because the IS terminal is connected to GND via an external resistor. Next, the voltage at the source of SW1 (= gate of output MOS) falls below the GND voltage. SW1 is turned on, and the clamp diode is connected to the gate of the output MOS, activating the dynamic clamp circuit.

When the over-voltage is applied to V_{CC} , the gate voltage and source voltage of SW1 are both nearly equal to GND. SW1 is not turned on, the clamp diode is not connected to the gate of the output MOS, and the dynamic clamp circuit is not activated.

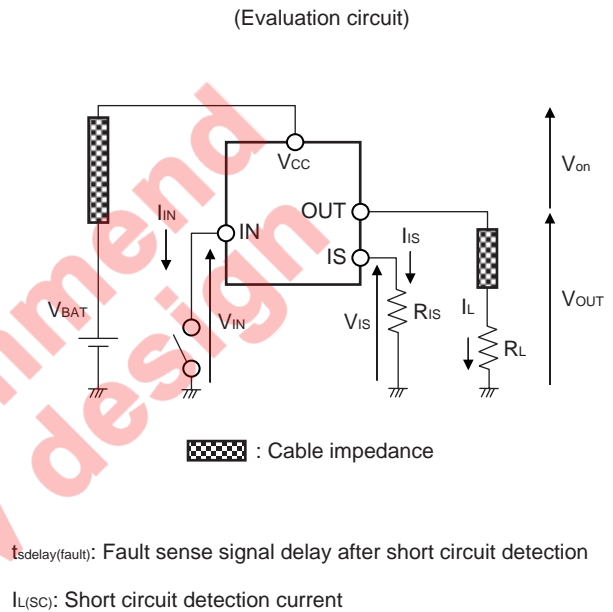
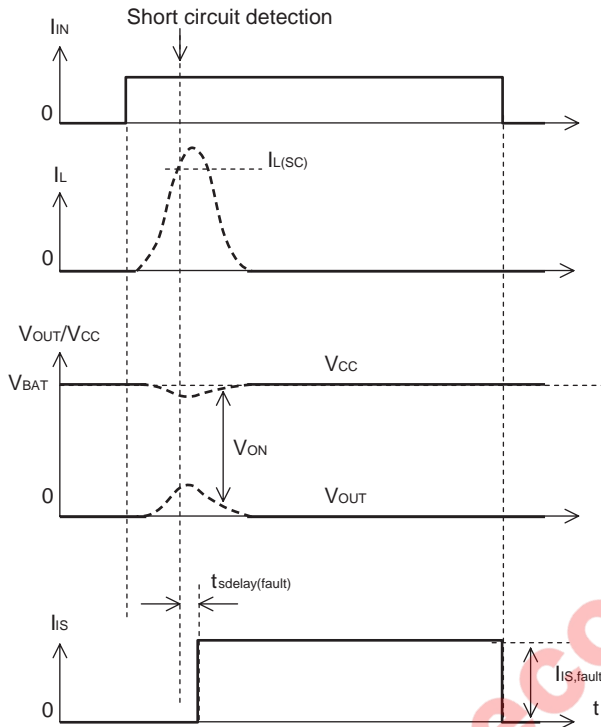
3.6.2 Short Circuit Protection

Case 1: I_{IN} pin is shorted to ground in an overload condition, which includes a short circuit condition.

The device shuts down automatically when either or both of following conditions (a, b) is detected. The sense current is fixed at $I_{IS, fault}$. Shutdown is latched until the next reset via input.

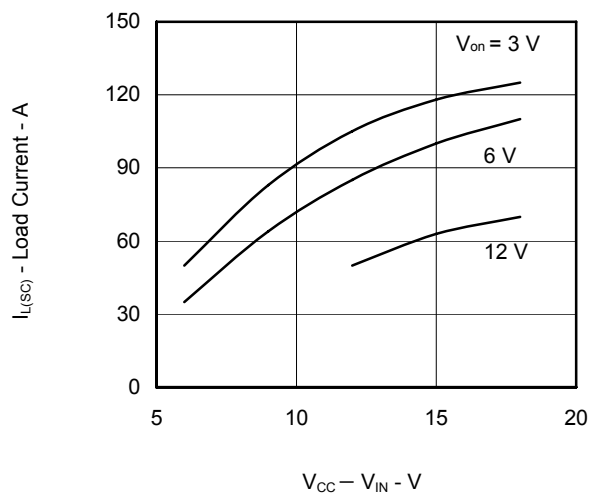
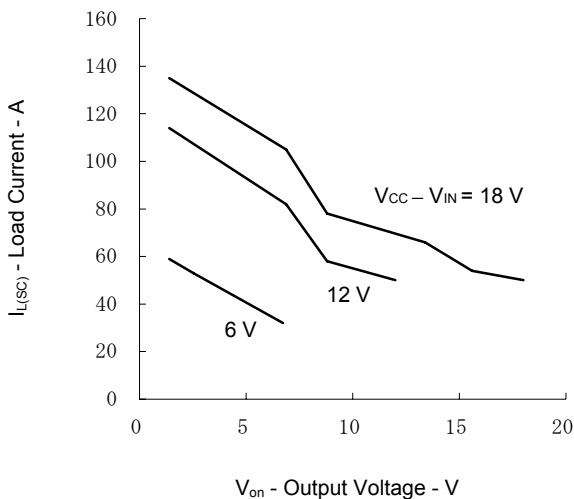
- (a) $I_L > I_{L(SC)}$
- (b) $V_{on} > V_{on(OVL)}$ after $t_{d(OC)}$

Case 1-(a) $I_L > I_{L(SC)}$

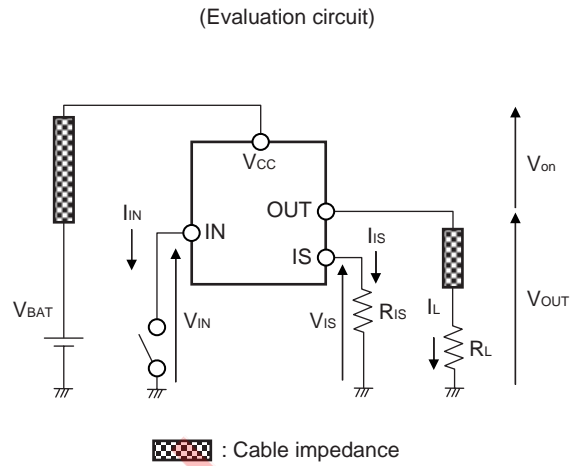
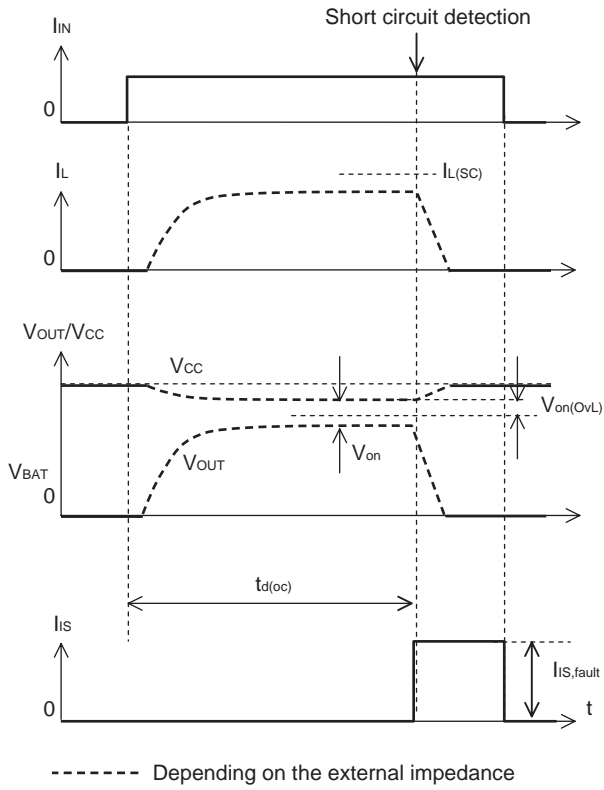


Typical Short circuit detection current characteristics

The short circuit detection current changes according V_{CC} voltage and V_{on} voltage for the purpose of to be strength of the robustness under short circuit condition.



Case 1-(b) $V_{on} > V_{on(OvL)}$ after $t_{d(OC)}$



$t_{d(OC)}$: Turn-on check delay after input current positive slope

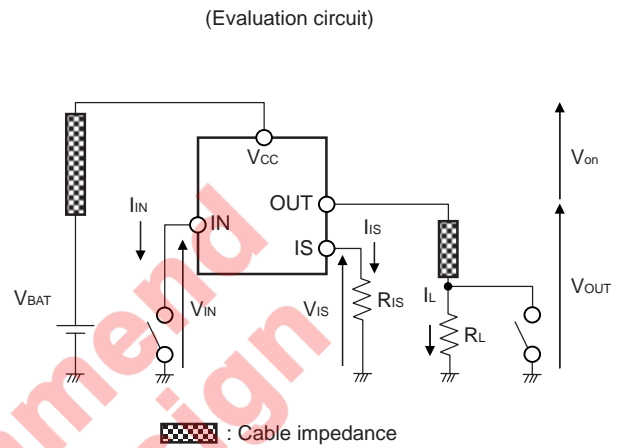
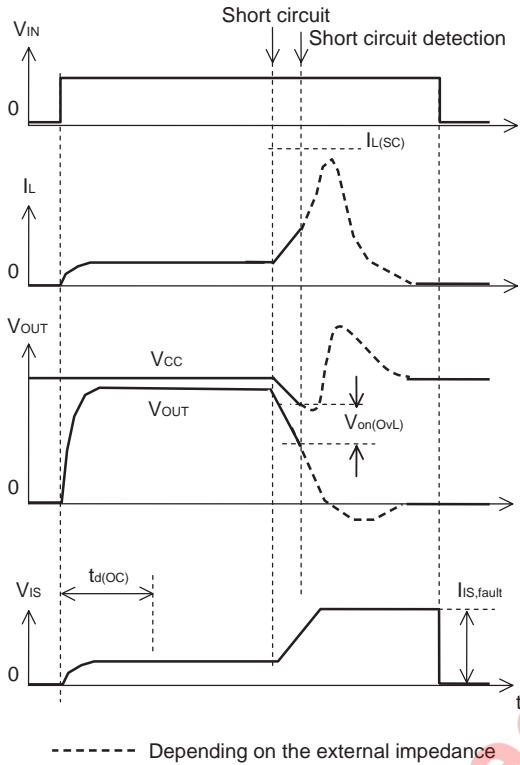
Not recommended for new design

Case 2: Short circuit during on-condition

The device shuts down automatically when following conditions (a) is detected. The sense current is fixed at $I_{IS, fault}$. Shutdown is latched until the next reset via input. In the case of $V_{on(NL)}$ works such open load condition at on-state, $t_{d(OC)}$ is expired.

(a) $V_{on} > V_{on(OvL)}$ after $t_{d(OC)}$

Case 2-(a) $V_{on} > V_{on(OvL)}$ after $t_{d(OC)}$



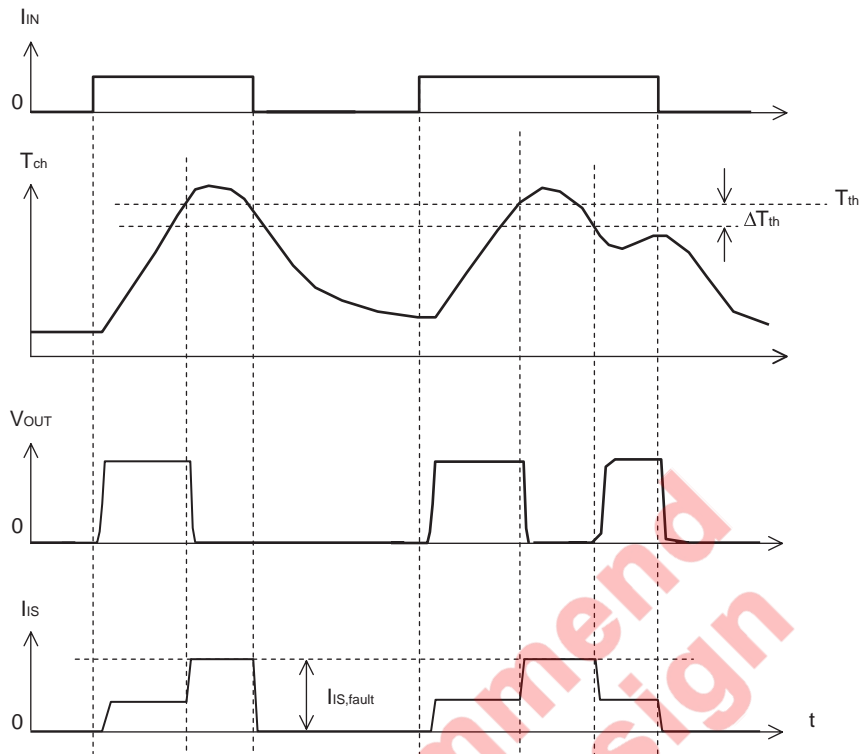
$t_{d(OC)}$: Turn-on check delay after input current positive slope

$I_{L(SC)}$: Short circuit detection current

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Over-temperature protection

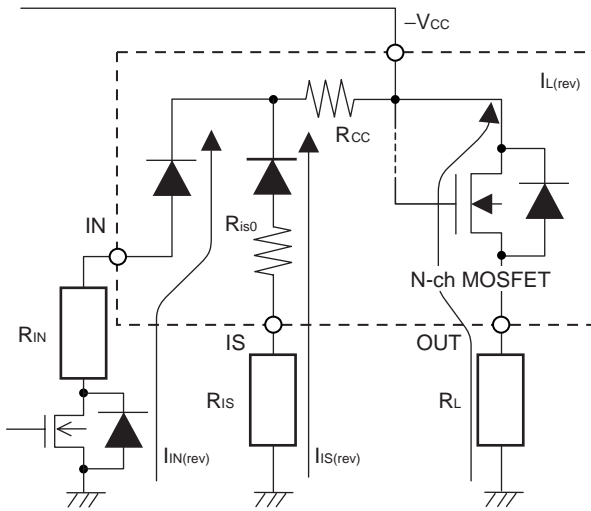
The output is switched off if over-temperature is detected. The device switches on again after it cools down.



Not recommended for new design

3.6.3 Power Dissipation under Reverse Battery Condition

In case of reverse battery condition, internal N-ch MOSFET is turned on to reduce the power dissipation by body diode. Additional power is dissipated by the internal resistor. Following is the formula for estimation of total power dissipation Pd(rev) in reverse battery condition.



$$P_{D(rev)} = R_{on(rev)} \times I_{L(rev)}^2 + (V_{CC} - V_f - I_{in(rev)} \times R_{IN}) \times I_{in(rev)} + (V_{CC} - I_{is(rev)} \times R_{IS}) \times I_{is(rev)}$$

$$I_{in(rev)} = (V_{CC} - 2 \times V_f) / (R_{CC} + R_{IN})$$

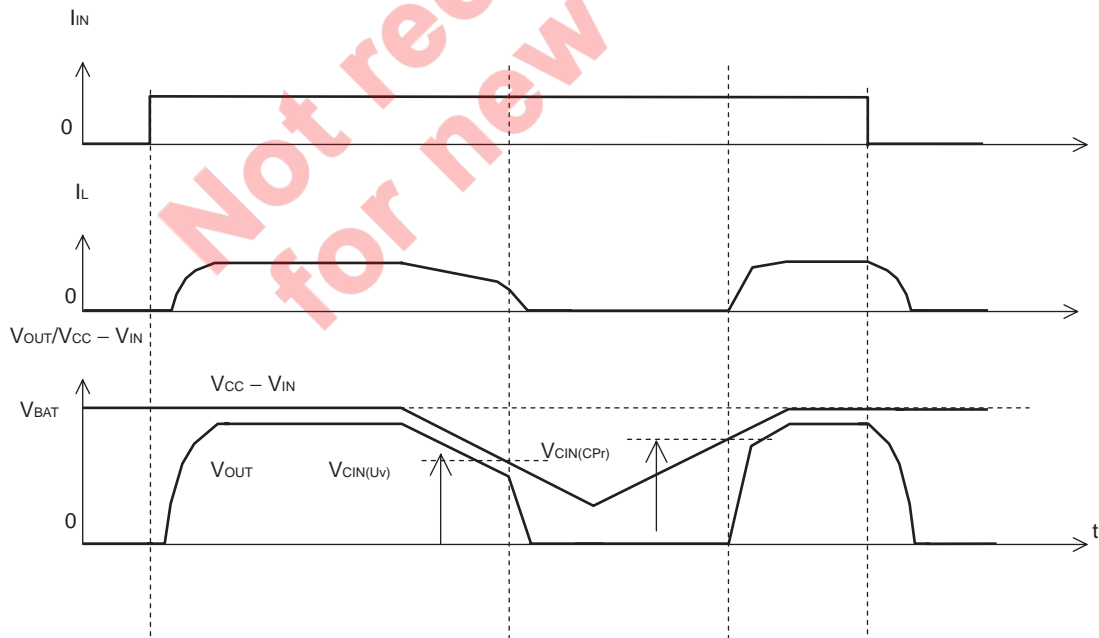
$$I_{is(rev)} = (V_{CC} - V_f) / (R_{CC} + R_{is0} + R_{IS})$$

The reverse current through the N-ch MOSFET has to be limited by the connected load.

$$R_{IN} < (|V_{CC} - 8 V|) / 0.08 A$$

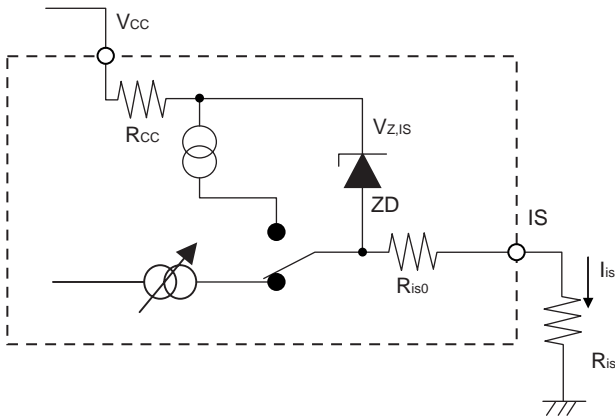
3.6.4 Device Behavior at Low Voltage Condition

If the supply voltage ($V_{CC} - V_{IN}$) goes down under $V_{CIN(UV)}$, the device shuts down the output. If supply voltage ($V_{CC} - V_{IN}$) increase over $V_{CIN(CPr)}$, the device turns on the output automatically. The device keeps off state if supply voltage ($V_{CC} - V_{IN}$) does not increase over $V_{CIN(CPr)}$ after under voltage shutdown. It is assumed that $V_{IN} = 0 V$ when I_{IN} is activated.

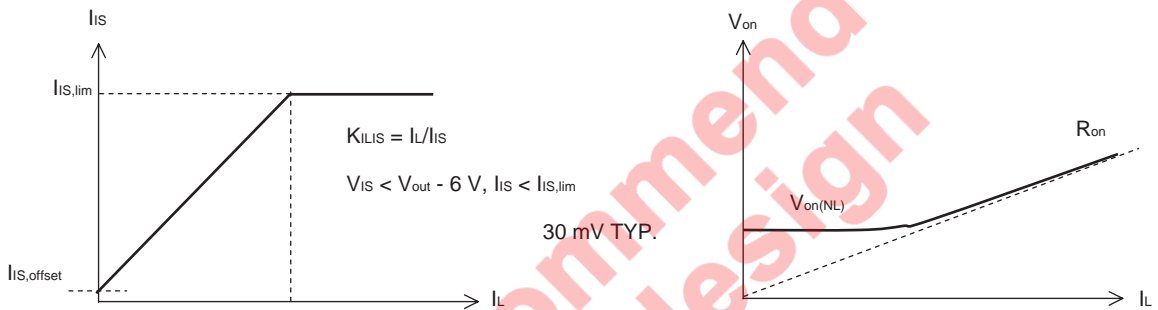


Remark It is assumed that $V_{IN} = 0 V$ when I_{IN} is activated.

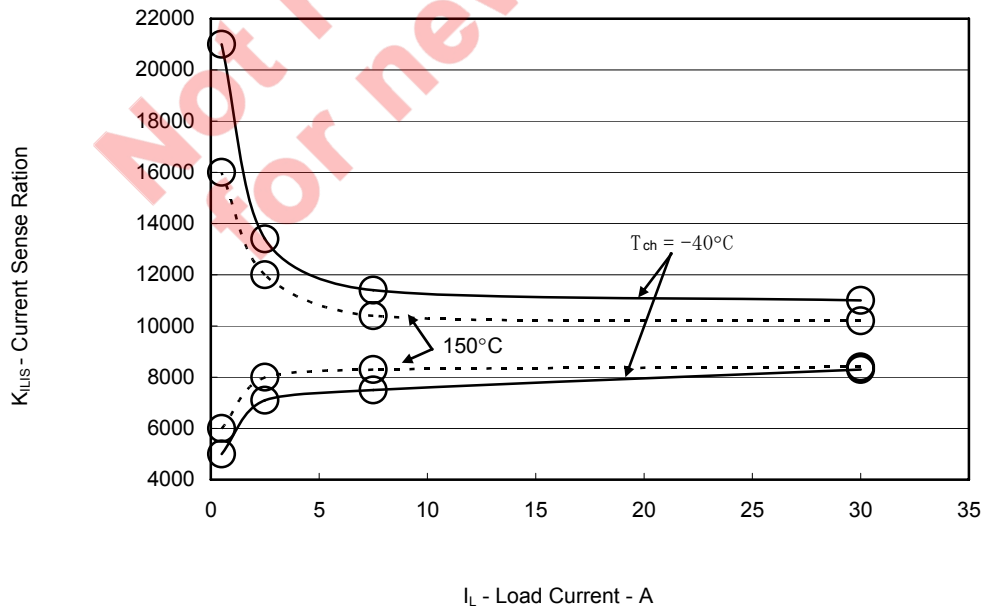
3.6.5 Current Sense Output



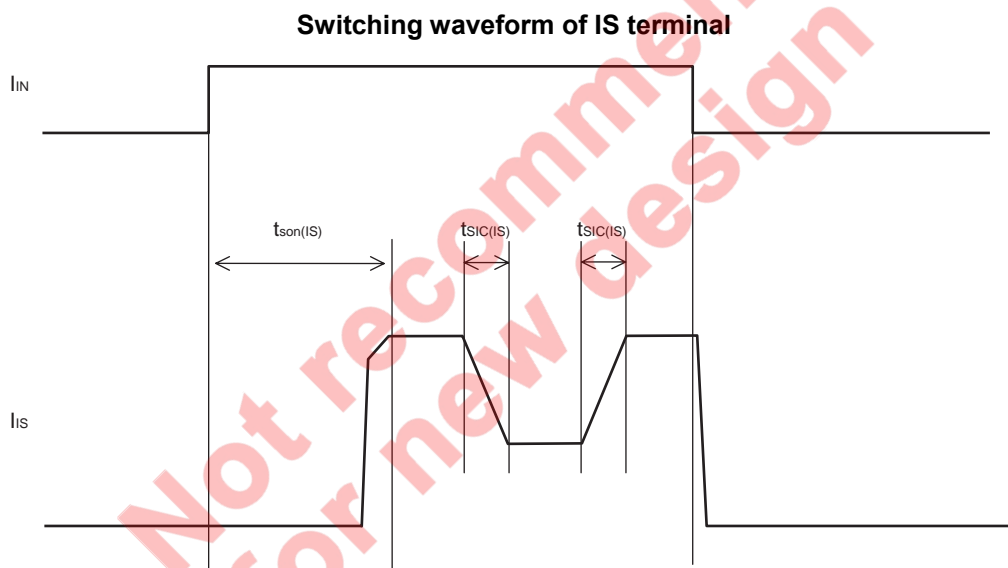
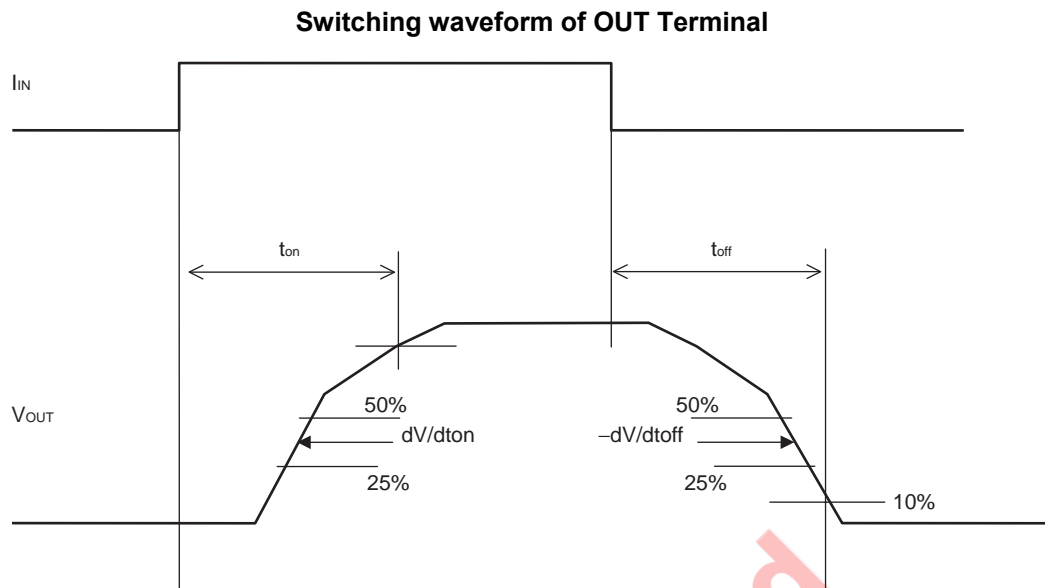
R_{cc} and R_{is0} are 100 Ω (TYP.). $V_{z,IS}$ = 46 V (TYP.), R_{is} = 1 kΩ nominal.



Current sense ratio



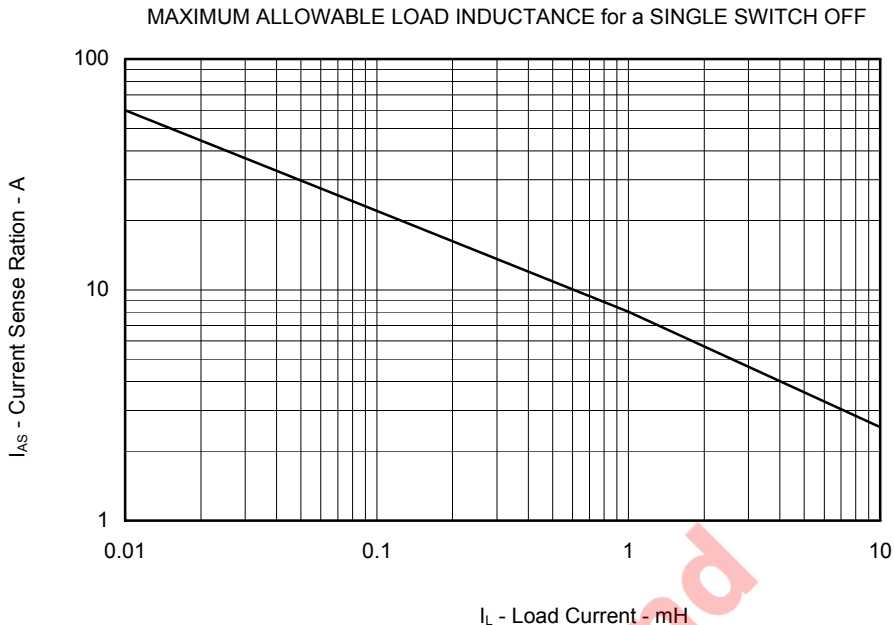
3.6.6 Measurement Condition



3.6.7 Truth Table

Input Current	State	Output	Sense Current
L	-	OFF	$I_{IS(LL)}$
H	Normal Operation	ON	I_L/K_{IIS}
	Over-temperature or Short circuit	OFF	$I_{IS,fault}$
	Open Load	ON	$I_{IS,offset}$

3.6.8 Inductive Load Switch Off Energy Dissipation for a Single Pulse

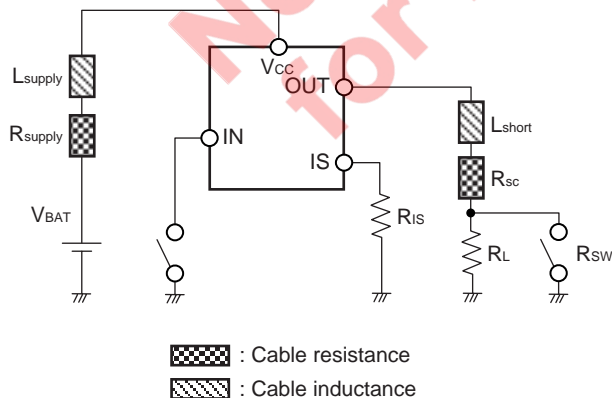


The energy dissipation for an inductive load switch-off single pulse in device (E_{AS1}) is estimated by the following formula as $R_L = 0 \Omega$.

$$E_{AS1} = \frac{1}{2} I^2 L \left[\frac{V_{on(CL)}}{V_{on(CL)} - V_{CC}} \right]$$

3.6.9 Maximum Allowable Switch off Energy (Single Pulse)

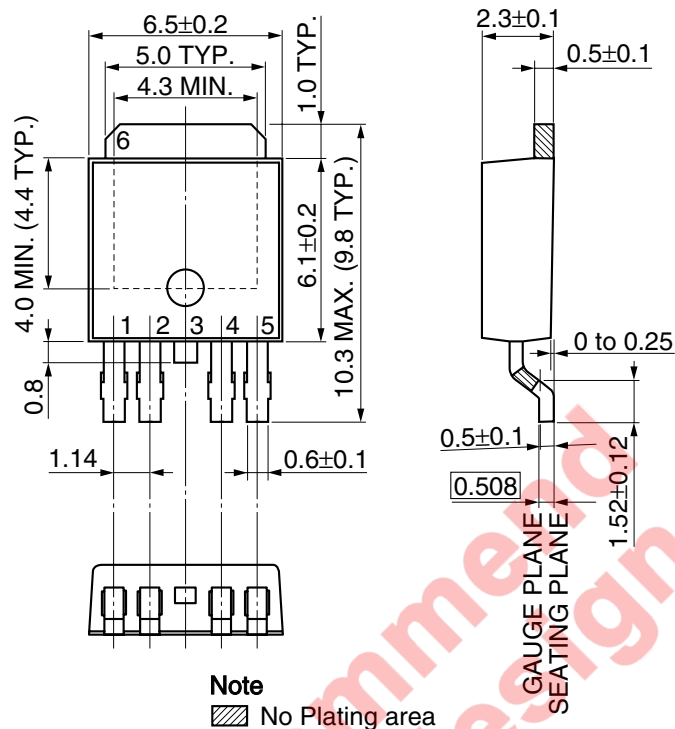
The harness connecting the power supply, the load and the device has a small inductance and resistance. When the device turns off, the energy stored in the harness inductance is dissipated by the device, the harness resistance and the internal resistance of power supply. If the current is abnormally high due to a load short, the energy stored in the harness can be large. This energy has to be taken into consideration for the safe operation. The following figure shows the condition for E_{AS2} , the maximum switch-off energy (single pulse) for abnormally high current.



$V_{BAT} = 18 \text{ V}$,
 $R_{supply} = 10 \text{ m}\Omega$, $R_{short} = R_{sc} + R_{SW(on)} = 50 \text{ m}\Omega$,
 $L_{supply} = 5 \text{ }\mu\text{H}$, $L_{short} = 15 \text{ }\mu\text{H}$,
 $T_{ch,start} \leq 150^\circ\text{C}$

3.7 Package Drawing (unit: mm)

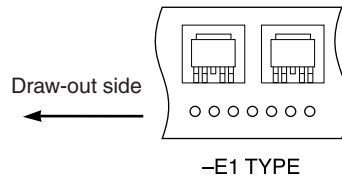
5-pin TO-252 (MP-3ZK)



Not recommended for new design

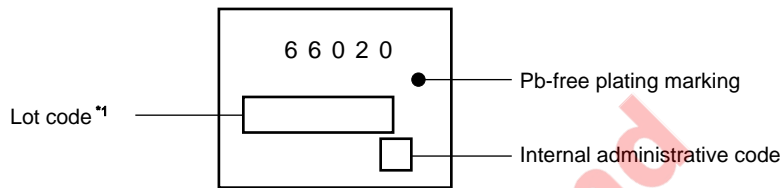
3.8 Taping Information

This is one type (E1) of direction of the device in the carrier tape.

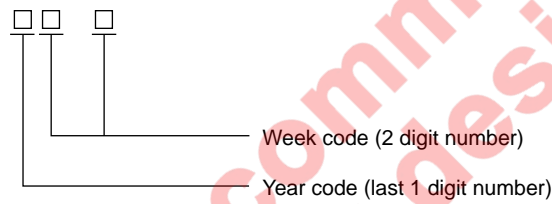


3.9 Marking Information

This figure indicates the marking items and arrangement. However, details of the letterform, the size and the position aren't indicated.



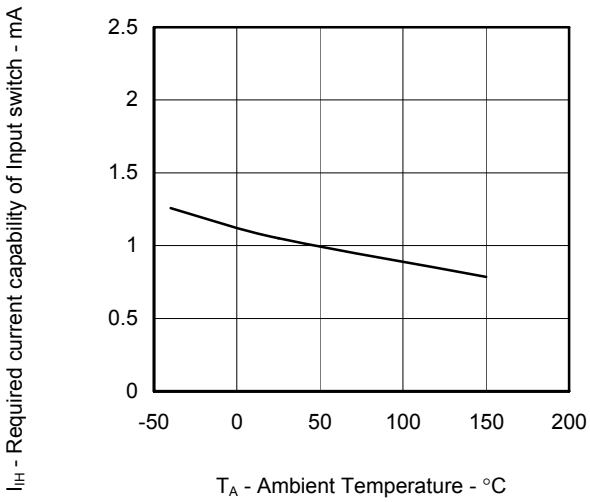
Note: *1. Composition of the lot code



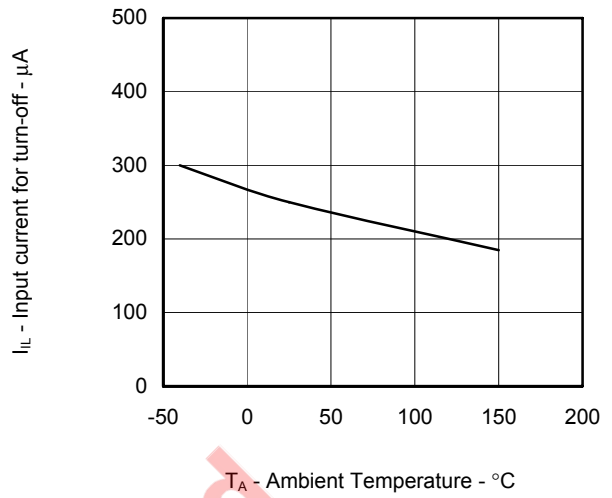
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4. Typical Characteristics

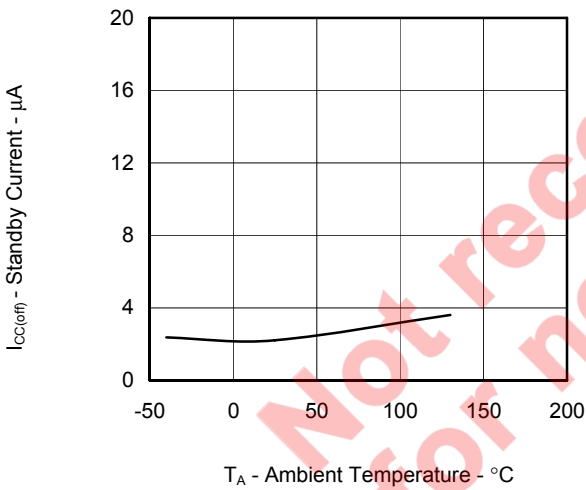
REQUIRED CURRENT CAPABILITY OF INPUT SWITCH vs. AMBIENT TEMPERATURE



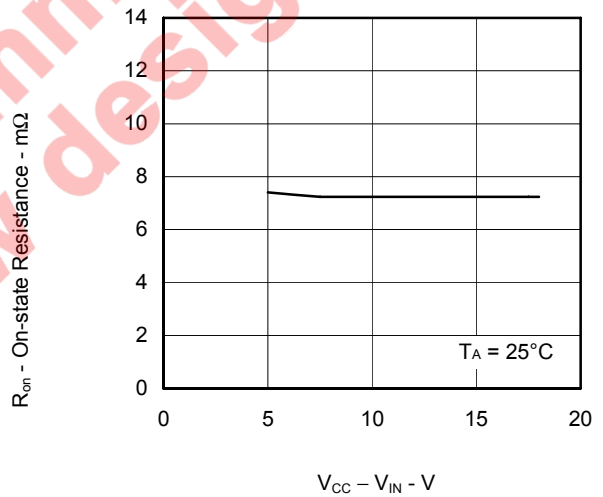
INPUT CURRENT FOR TURN OFF vs. AMBIENT TEMPERATURE



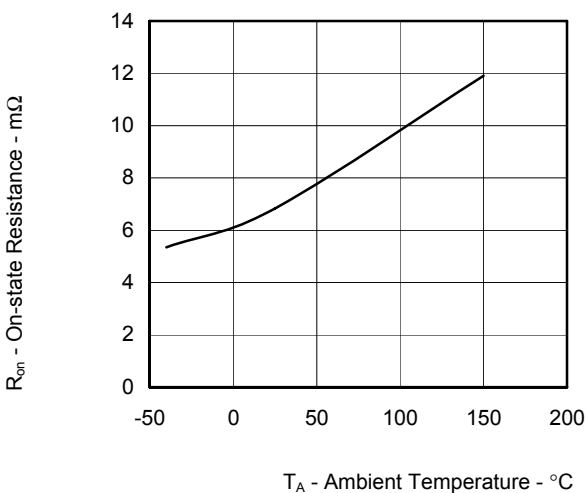
STANDBY CURRENT vs. AMBIENT TEMPERATURE



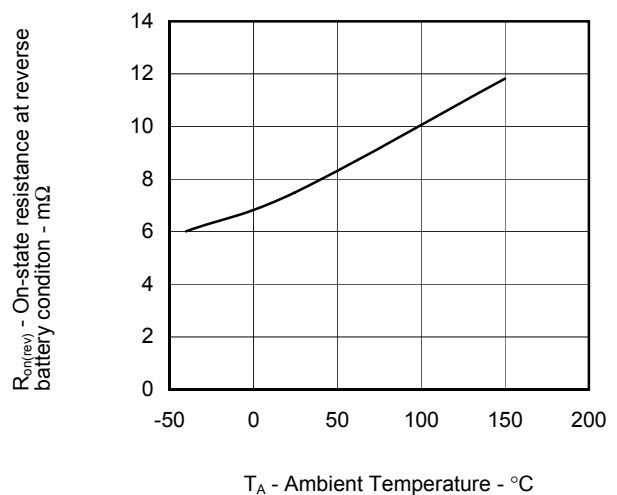
ON STATE RESISTANCE vs. V_{CC} - V_{IN} voltage



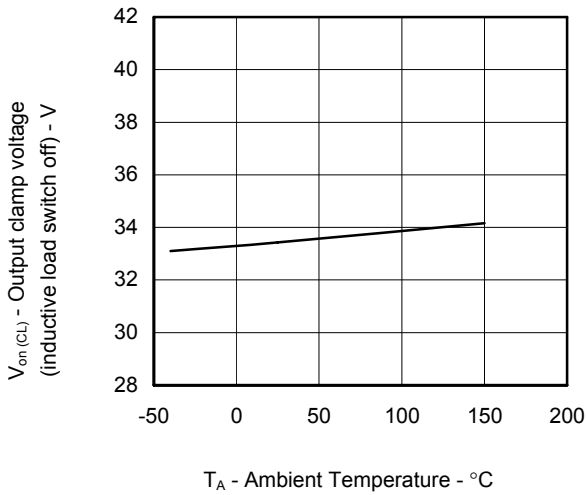
ON STATE RESISTANCE vs. AMBIENT TEMPERATURE



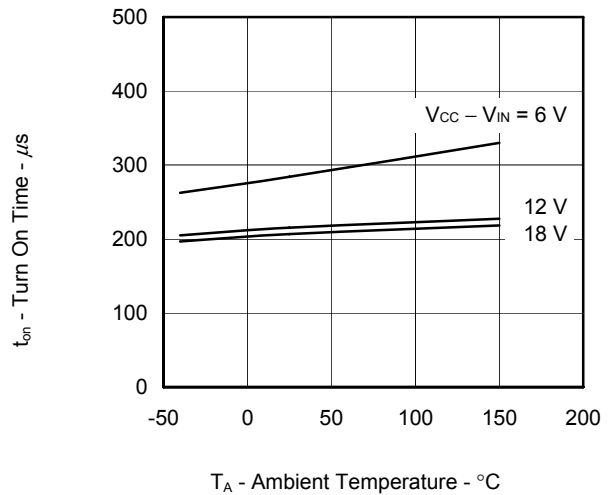
ON STATE RESISTANCE AT REVERSE BATTERY CONDITION vs. AMBIENT TEMPERATURE



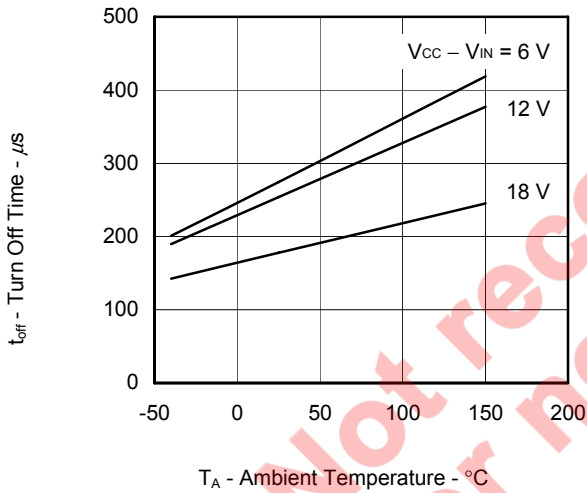
OUTPUT CLAMP VOLTAGE (INDUCTIVE LOAD SWITCH OFF) vs. AMBIENT TEMPERATURE



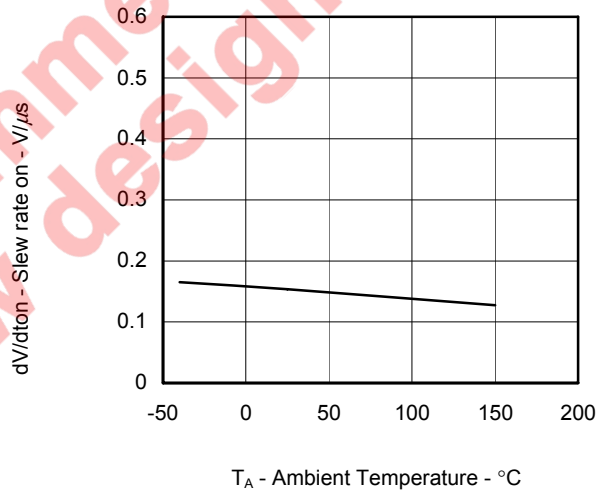
TURN ON TIME vs. AMBIENT TEMPERATURE



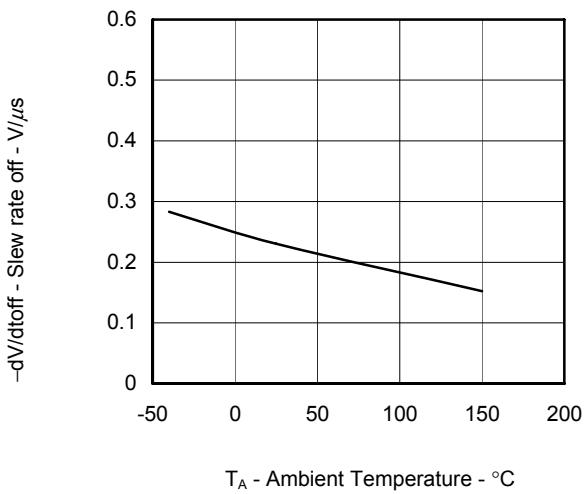
TURN OFF TIME vs. AMBIENT TEMPERATURE



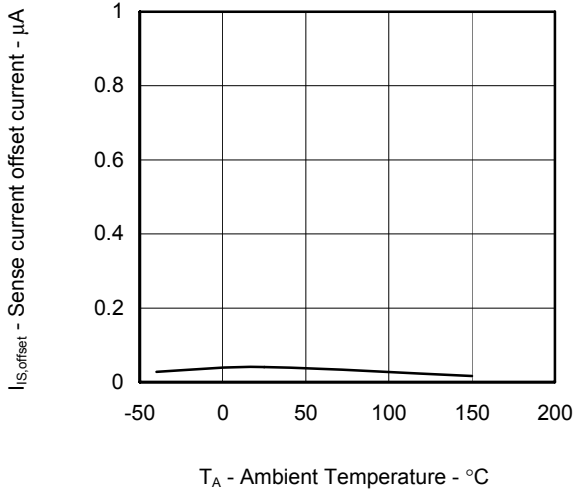
SLEW RATE ON vs. AMBIENT TEMPERATURE



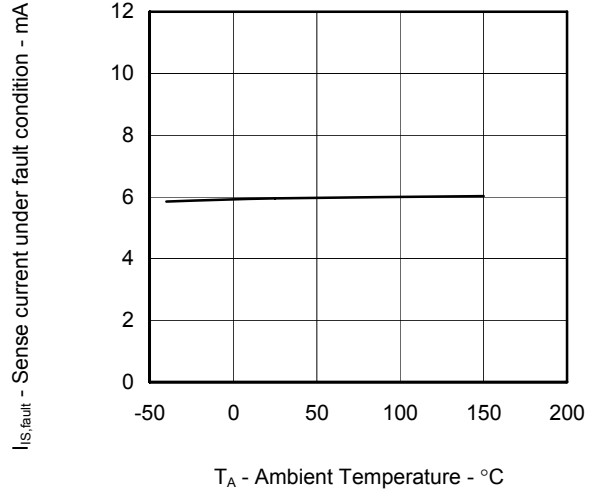
SLEW RATE OFF vs. AMBIENT TEMPERATURE



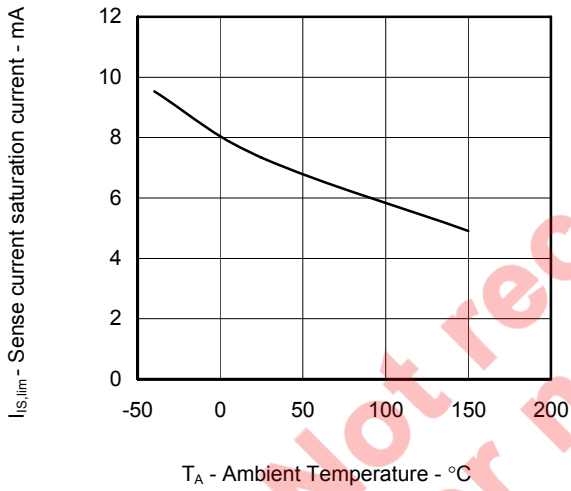
SENSE CURRENT OFFSET CURRENT vs. AMBIENT TEMPERATURE



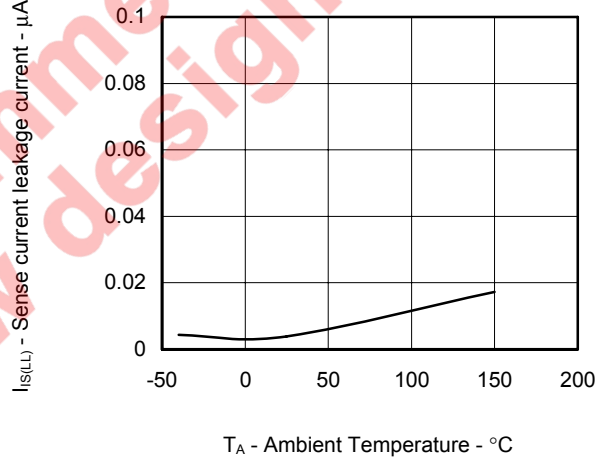
SENSE CURRENT UNDER FAULT CONDITION vs. AMBIENT TEMPERATURE



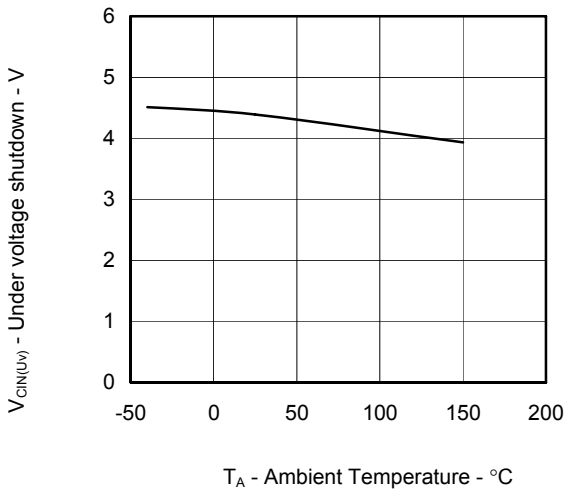
SENSE CURRENT SATURATION CURRENT vs. AMBIENT TEMPERATURE



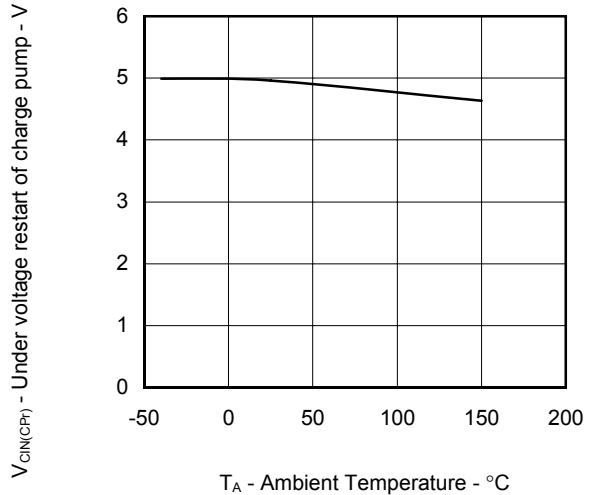
SENSE CURRENT LEAKAGE CURRENT vs. AMBIENT TEMPERATURE



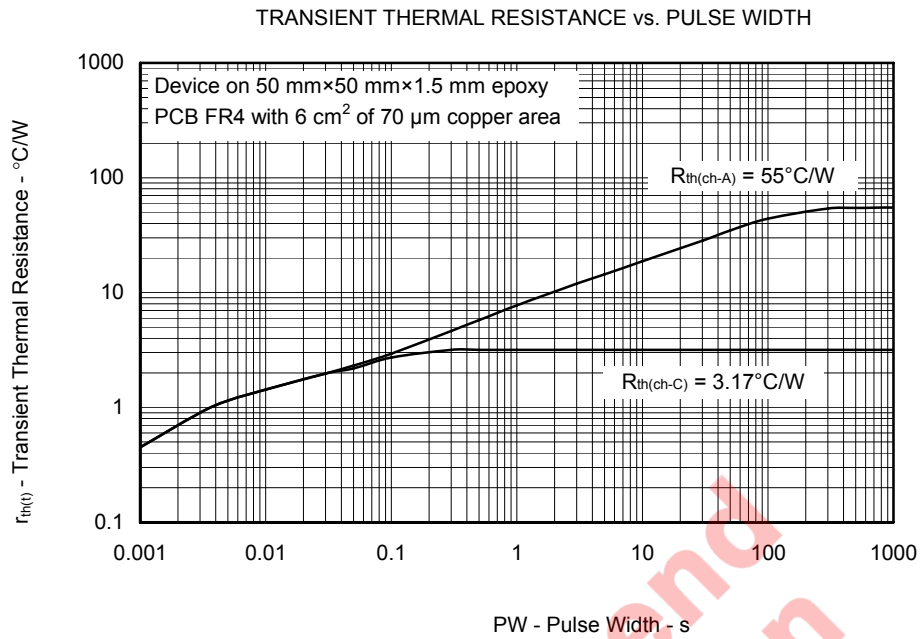
UNDER VOLTAGE SHUTDOWN vs. AMBIENT TEMPERATURE



UNDER VOLTAGE RESTART OF CHARGE PUMP vs. AMBIENT TEMPERATURE

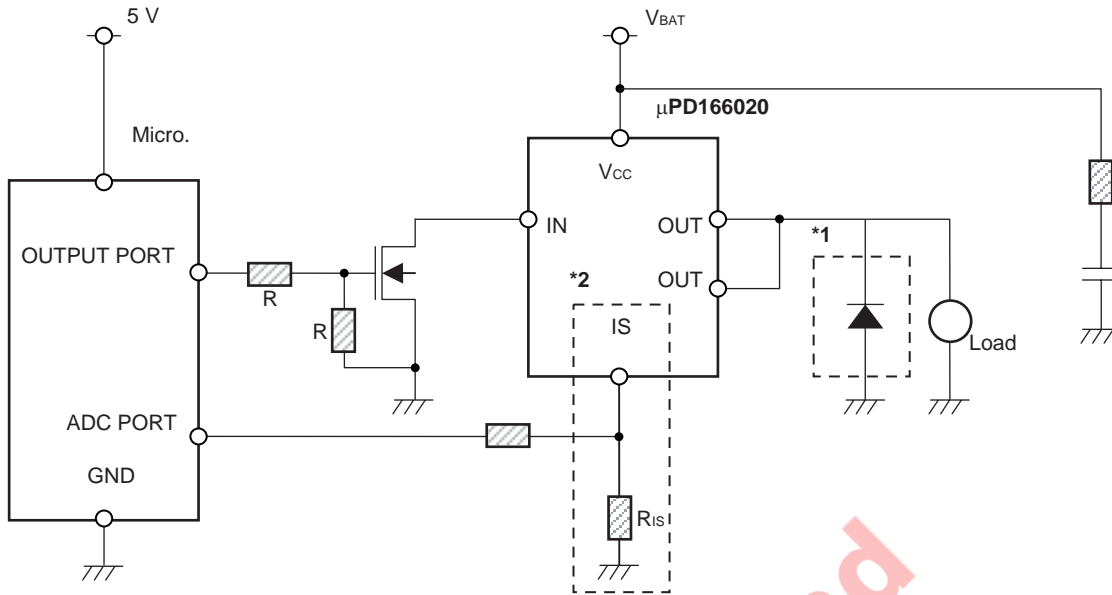


5. Thermal Characteristics



Not recommended for new design

6. Application Example in Principle



- Notes: *1. If output current is over the maximum allowable current for inductive load at a single switch off, or if energy at a single switch off is over E_{AS1}/E_{AS2} , then a free wheeling diode must be connected in parallel the load.
- *2. If current sense and diagnostic features are not used, IS terminal has to be connected to GND via resistor.

Not recommended
for new design

Revision History	μPD166020T1F Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Aug 15, 2011	-	First Edition Issued

**Not recommend
for new design**

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